

Product Summary

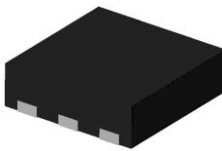
BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
30V	28mΩ @ V _{GS} = 10V	7.0A
	32mΩ @ V _{GS} = 4.5V	6.5A

Description and Applications

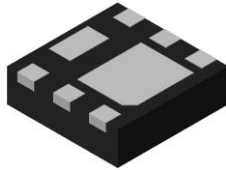
This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions

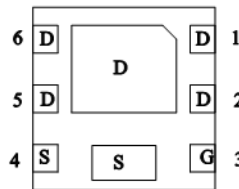
U-DFN2020-6
(Type F)



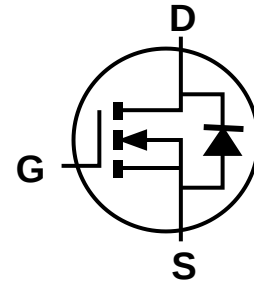
Top View



Bottom View



Pin Out
Bottom View



Internal Schematic

Features and Benefits

- 0.6mm Profile – Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

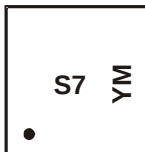
- Case: U-DFN2020-6 (Type F)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 Per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.007 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3042LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3042LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



S7 = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: D = 2016)
M = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022	2023
Code	D	E	F	G	H	I	J	K

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	7.0 5.6	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	1.5	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	35	A
Avalanche Current (L = 0.1mH) (Note 7)			I _{AS}	13	A
Avalanche Energy (L = 0.1mH) (Note 7)			E _{AS}	9	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	177	°C/W
	t < 10s		124	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	61	°C/W
	t < 10s		43	
Thermal Resistance, Junction to Case	Steady State	R _{θJC}	9.3	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.6	—	1.4	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	17	28	mΩ	V _{GS} = 10V, I _D = 4.0A
		—	20	32		V _{GS} = 4.5V, I _D = 4.0A
		—	24	42		V _{GS} = 3.0V, I _D = 4.0A
		—	28	50		V _{GS} = 2.5V, I _D = 4.0A
		—	—	—		V _{GS} = 0V, I _S = 1A
Diode Forward Voltage	V _{SD}	—	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	570	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	63	—		
Reverse Transfer Capacitance	C _{rss}	—	53	—		
Gate Resistance	R _g	—	3.2	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = 10V)	Q _g	—	13.3	—	nC	V _{DS} = 15V, I _D = 6.9A
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	6.1	—		
Gate-Source Charge	Q _{gs}	—	1.0	—		
Gate-Drain Charge	Q _{gd}	—	1.6	—		
Turn-On Delay Time	t _{D(ON)}	—	1.5	—	ns	V _{GS} = 10V, V _{DD} = 15V, R _G = 3Ω, I _D = 6.9A
Turn-On Rise Time	t _r	—	3.3	—		
Turn-Off Delay Time	t _{D(OFF)}	—	13.9	—		
Turn-Off Fall Time	t _f	—	4.9	—		
Body Diode Reverse Recovery Time	t _{RR}	—	7.8	—	ns	I _S = 5A, dI/dt = 100A/μs
Body Diode Reverse Recovery Charge	Q _{RR}	—	1.9	—	nC	I _S = 5A, dI/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep T_J = +25°C.
 8. Short duration pulse test used to minimize self-heating effect.
 9. Guaranteed by design. Not subject to product testing.

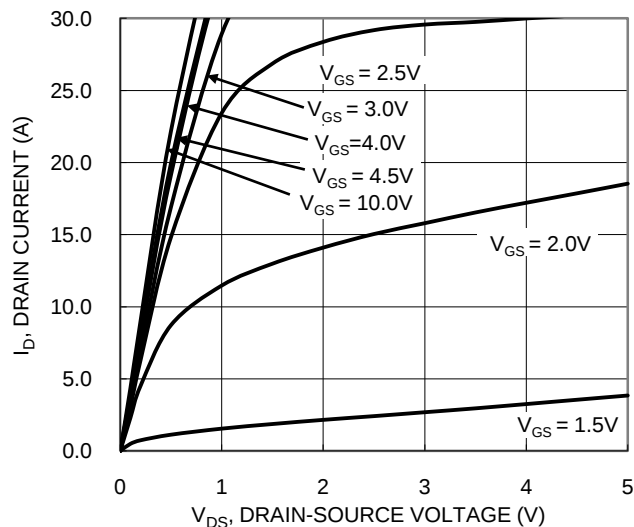


Figure 1. Typical Output Characteristic

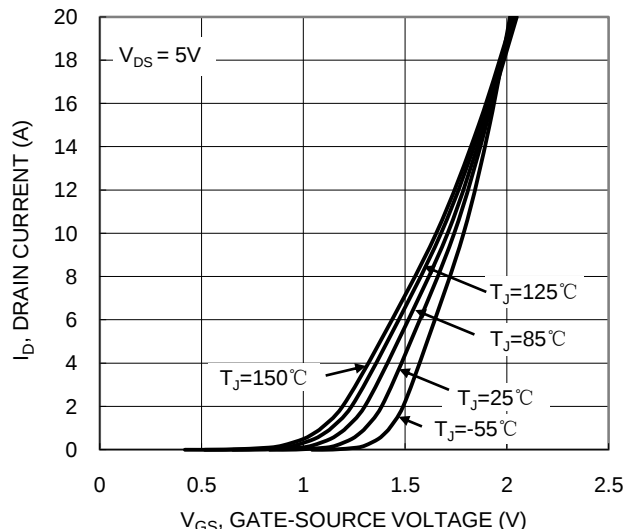


Figure 2. Typical Transfer Characteristic

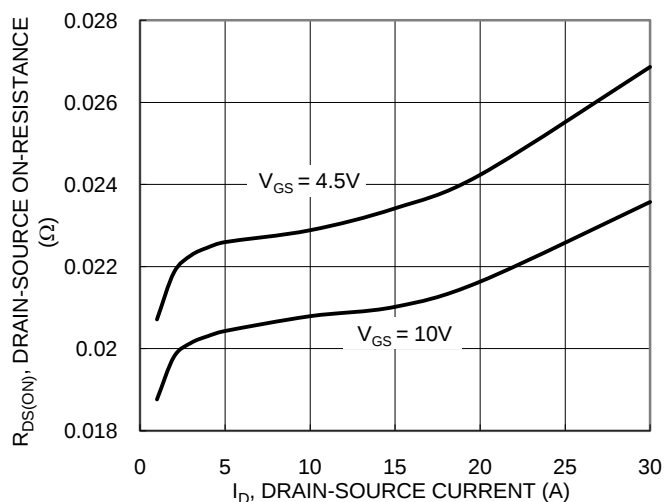


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

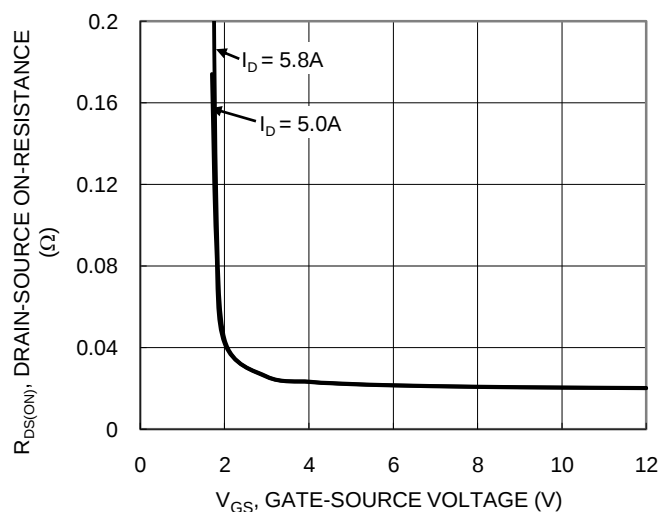


Figure 4. Typical Transfer Characteristic

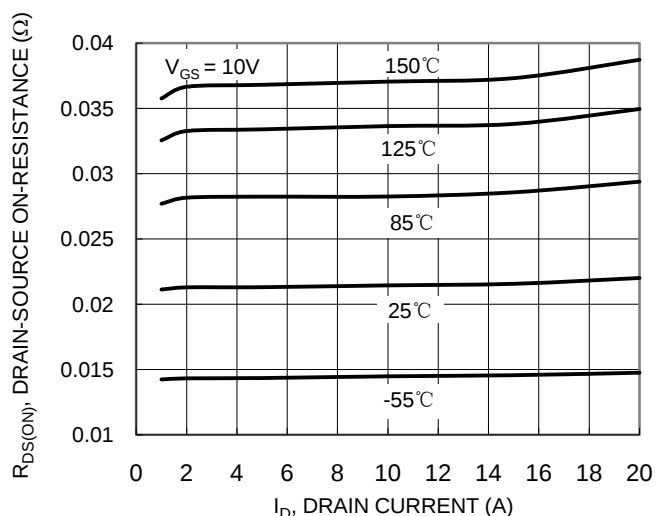


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

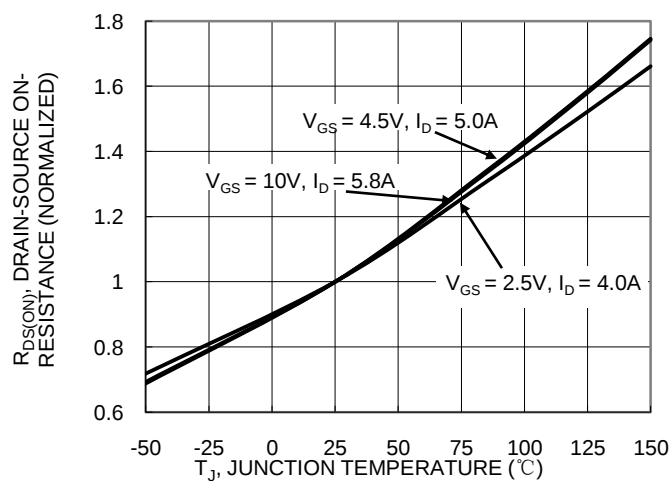


Figure 6. On-Resistance Variation with Temperature

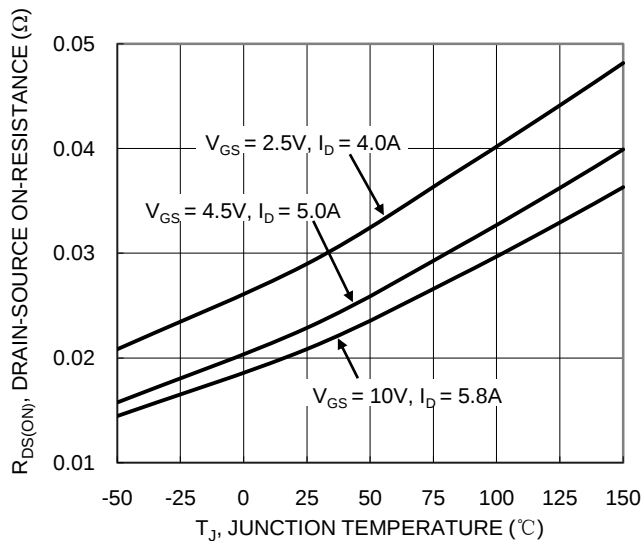


Figure 7. On-Resistance Variation with Temperature

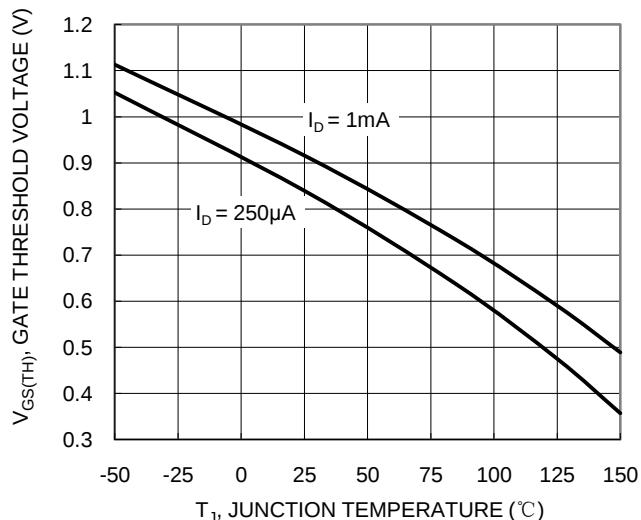


Figure 8. Gate Threshold Variation vs. Temperature

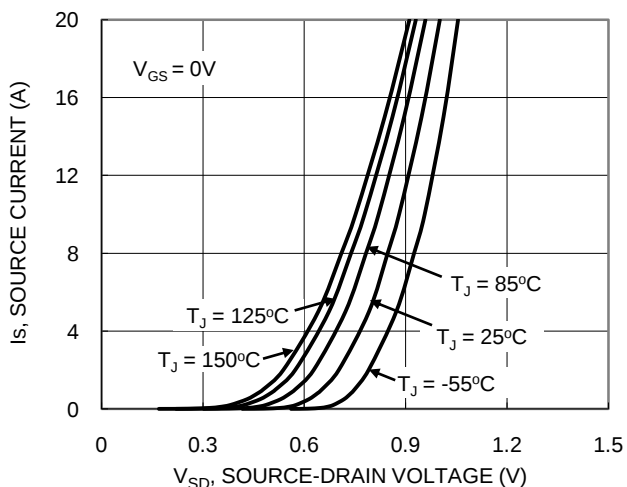


Figure 9. Diode Forward Voltage vs. Current

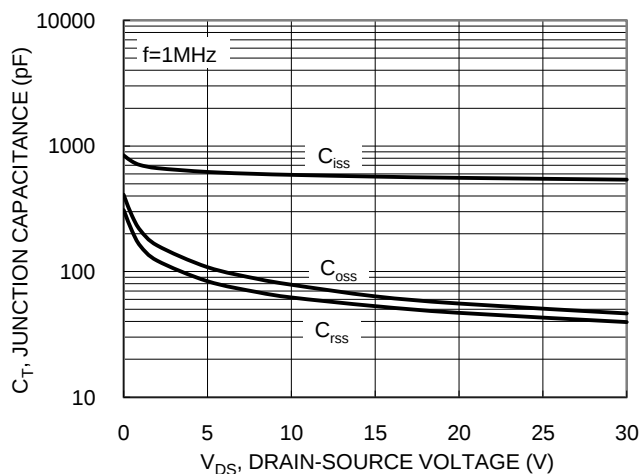


Figure 10. Typical Junction Capacitance

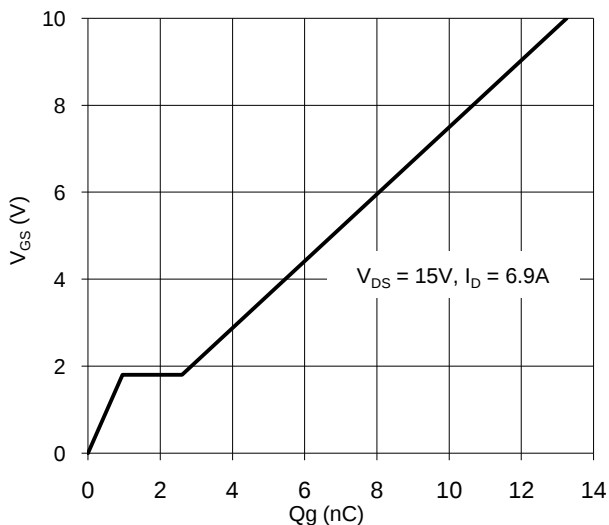


Figure 11. Gate Charge

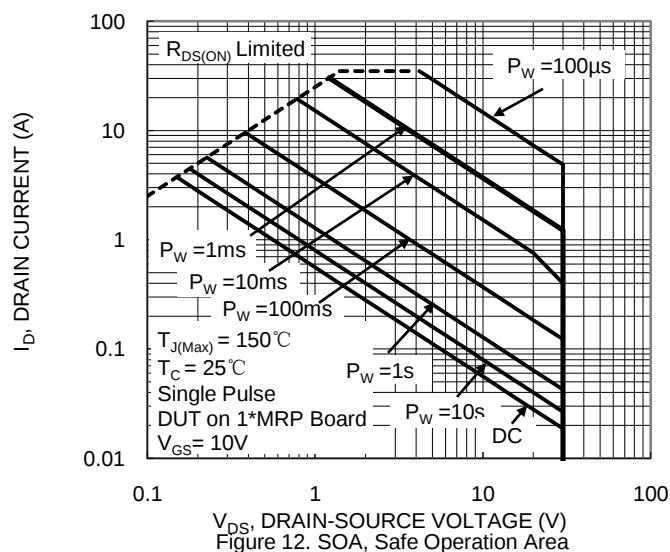


Figure 12. SOA, Safe Operation Area

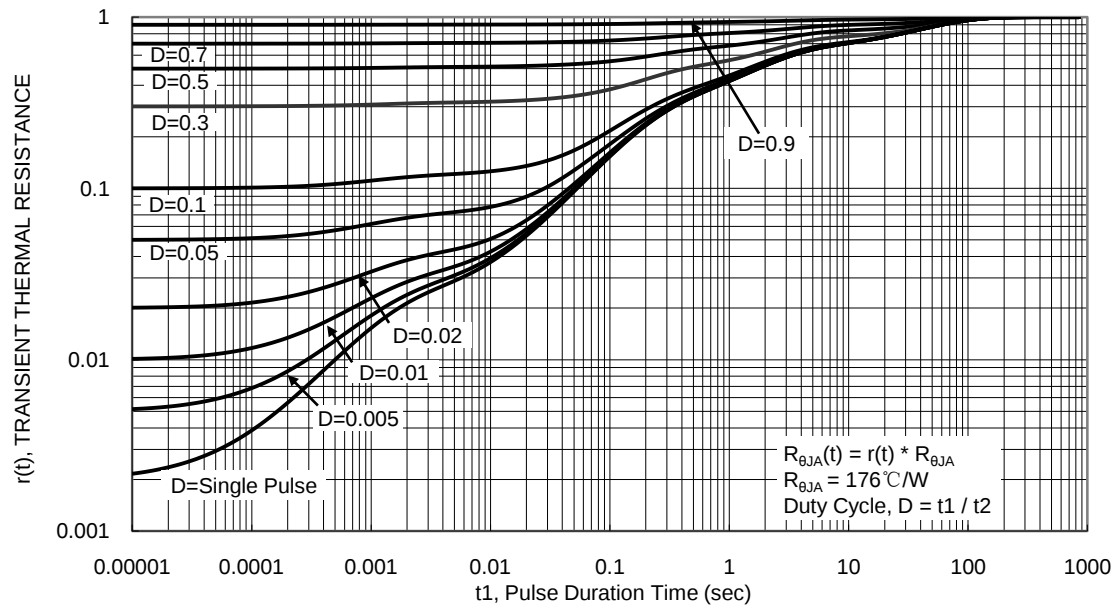
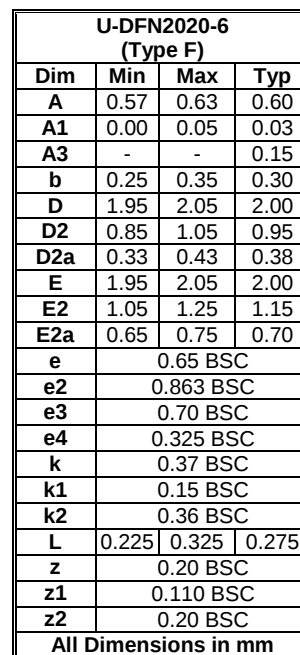


Figure 13. Transient Thermal Resistance

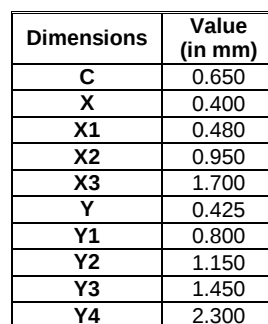
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U-DFN2020-6 (Type F)



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